

89 [0056] ABSTRACT OF THE DISCLOSURE

90 [0057] Disclosed is a method of forming a thick silicon oxide layer upon or
91 internal to a silicon structure. The method is particularly useful in creating isolation
92 regions within a silicon-containing structure, where such isolation regions can withstand
93 high voltages. The electrically isolating thick silicon oxide layer or isolation regions can
94 be shaped, machined, or etched to provide feedthroughs for vertical or horizontal
95 interconnects. The feedthroughs may be coated with metal or filled with metal to
96 provide the interconnect.

[illegible]